

Tentative data

Insulated Gate Bi-Polar Transistor

Type T0960VC17G

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{CES}	Collector – emitter voltage	1700	V
$V_{DC\ link}$	Permanent DC voltage for 100 FIT failure rate.	900	V
V_{GES}	Peak gate – emitter voltage	± 20	V

	RATINGS	MAXIMUM LIMITS	UNITS
I_C	DC collector current, IGBT	960	A
I_{CRM}	Repetitive peak collector current, $t_p=1ms$, IGBT	1920	A
$I_{F(DC)}$	Continuous DC forward current, Diode	960	A
I_{FRM}	Repetitive peak forward current, $t_p=1ms$, Diode	1920	A
I_{FSM}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}=60\%V_{RRM}$, Diode (Note 4)	5635	A
I_{FSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}\leq 10V$, Diode (Note 4)	6200	A
P_{MAX}	Maximum power dissipation, IGBT (Note 2)	2.96	kW
$(di/dt)_{cr}$	Critical diode di/dt (note 3)	6000	A/ μs
T_j	Operating temperature range.	-40 to +125	$^{\circ}C$
T_{stg}	Storage temperature range.	-40 to +125	$^{\circ}C$

Notes: -

- 1) Unless otherwise indicated $T_j = 125^{\circ}C$.
- 2) $T_{sink} = 25^{\circ}C$, double side cooled.
- 3) Maximum commutation loop inductance 150nH.
- 4) Half-sinewave, $125^{\circ}C$ T_j initial.

Characteristics

IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V _{CE(sat)}	Collector – emitter saturation voltage	-	2.36	2.65	I _C = 960A, V _{GE} = 15V, T _j = 25°C	V
		-	3.0	3.3	I _C = 960A, V _{GE} = 15V	V
V _{T0}	Threshold voltage	-	-	1.22	Current range: 320A – 960A	V
r _T	Slope resistance	-	-	2.17		mΩ
V _{GE(TH)}	Gate threshold voltage	-	5	-	V _{CE} = V _{GE} , I _C = 32mA	V
I _{CES}	Collector – emitter cut-off current	-	5.5	15	V _{CE} = V _{CES} , V _{GE} = 0V	mA
I _{GES}	Gate leakage current	-	-	±15	V _{GE} = ±20V	µA
C _{ies}	Input capacitance	-	75	-	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	nF
t _{d(on)}	Turn-on delay time	-	0.32	-	I _C = 960A, V _{CE} = 900V, di/dt = 5000A/µs	µs
t _{r(V)}	Rise time	-	0.84	-		µs
Q _{g(on)}	Turn-on gate charge	-	4.2	-	V _{GE} = ±15V, L _S = 120nH	µC
E _{on}	Turn-on energy	-	0.47	-	R _{g(ON)} = 2Ω, R _{g(OFF)} = 15Ω, C _{GE} = 120nF	J
t _{d(off)}	Turn-off delay time	-	2.1	-	Integral diode used as freewheel diode (Note 3 & 4)	µs
t _{f(l)}	Fall time	-	0.55	-		µs
Q _{g(off)}	Turn-off gate charge	-	2.4	-		µC
E _{off}	Turn-off energy	-	0.8	-		J
I _{sc}	Short circuit current	-	2400	-	V _{GE} = +15V, V _{CC} = 900V, V _{CEmax} ≤ V _{CES} , t _p ≤ 10µs	A

Diode Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V _F	Forward voltage	-	1.95	2.25	I _F = 960A, T _j = 25°C	V
		-	2.05	2.35	I _F = 960A	V
V _{To}	Threshold voltage	-	-	1.37	Current range 320A - 960A	V
r _T	Slope resistance	-	-	1.02		mΩ
I _{rm}	Peak reverse recovery current	-	540	-	I _F = 960A, V _r = 900V, V _{GE} = -15V, di/dt = 5000A/µs	A
Q _{rr}	Recovered charge	-	310	-		µC
t _{rr}	Reverse recovery time, 50% chord	-	0.6	-		µs
E _r	Reverse recovery energy	-	0.18	-		J

Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R _{thJK}	Thermal resistance junction to sink, IGBT	-	-	33.8	Double side cooled	K/kW
		-	-	51.8	Collector side cooled	K/kW
		-	-	96.9	Emitter side cooled	K/kW
R _{thJK}	Thermal resistance junction to sink, Diode	-	-	36.1	Double side cooled	K/kW
		-	-	55.6	Cathode side cooled	K/kW
		-	-	104	Anode side cooled	K/kW
F	Mounting force	11	-	16	Note 2	kN
W _t	Weight	-	0.65	-		kg

Notes:-

- 1) Unless otherwise indicated T_j = 125°C.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C_{GE} is additional gate – emitter capacitance added to output of gate drive
- 4) Figures 6 to 9 are obtained using integral diode as freewheeling diode

Curves

Figure 1 – Typical collector-emitter saturation voltage characteristics

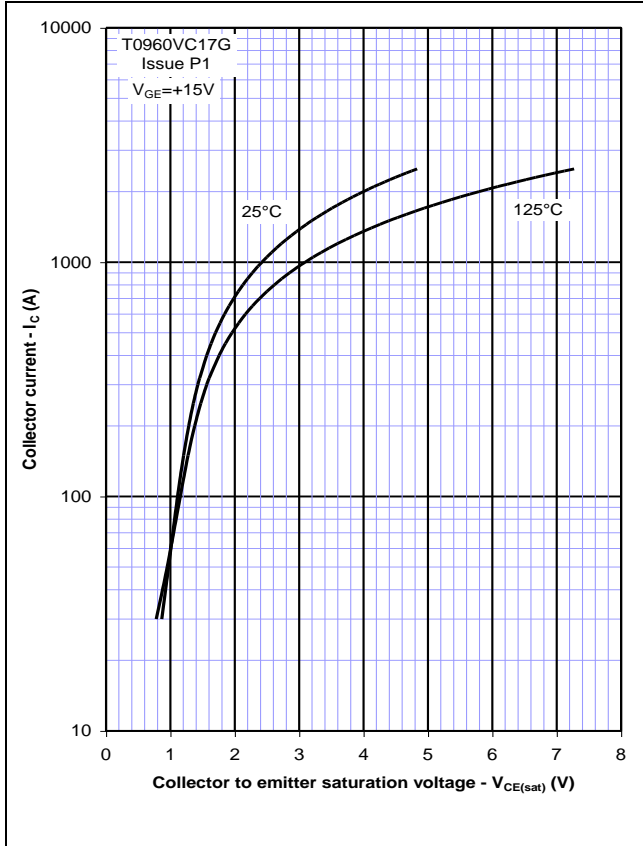


Figure 2 – Typical output characteristic

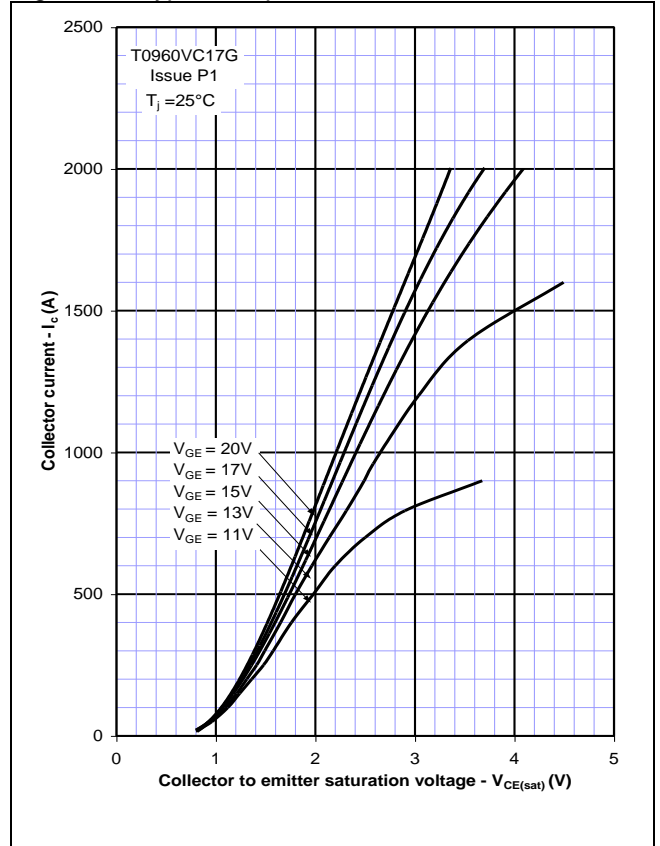


Figure 3 – Typical output characteristic

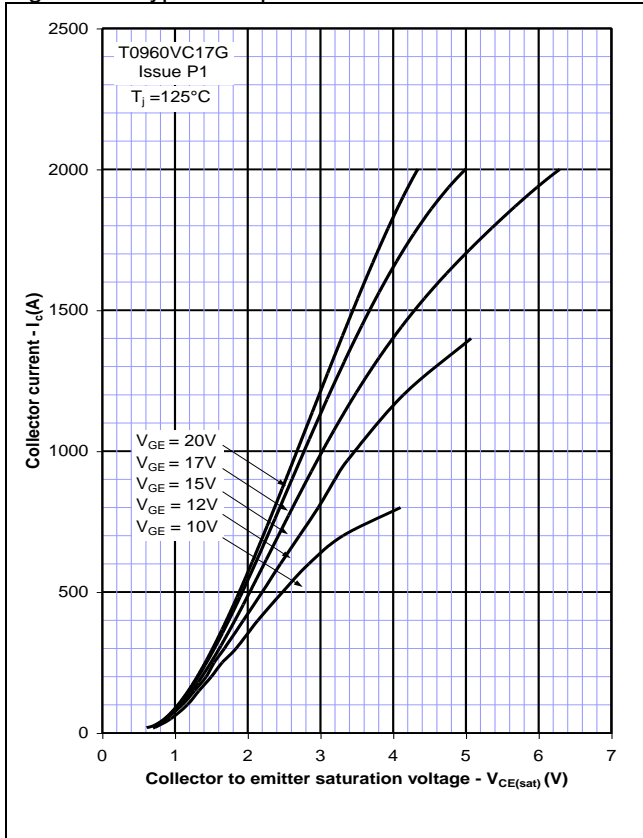


Figure 4 – Safe operating area (IGBT)

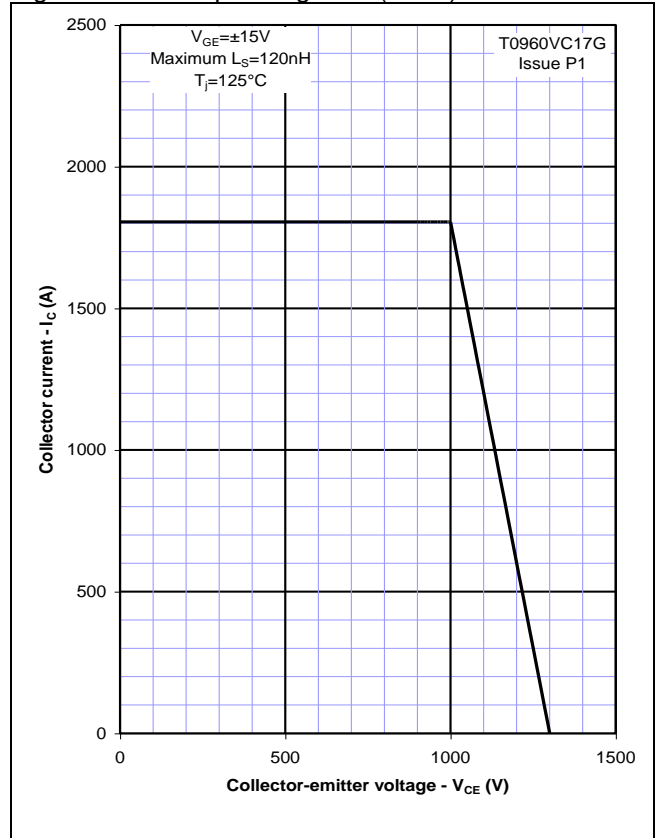


Figure 5 – Typical diode forward characteristics

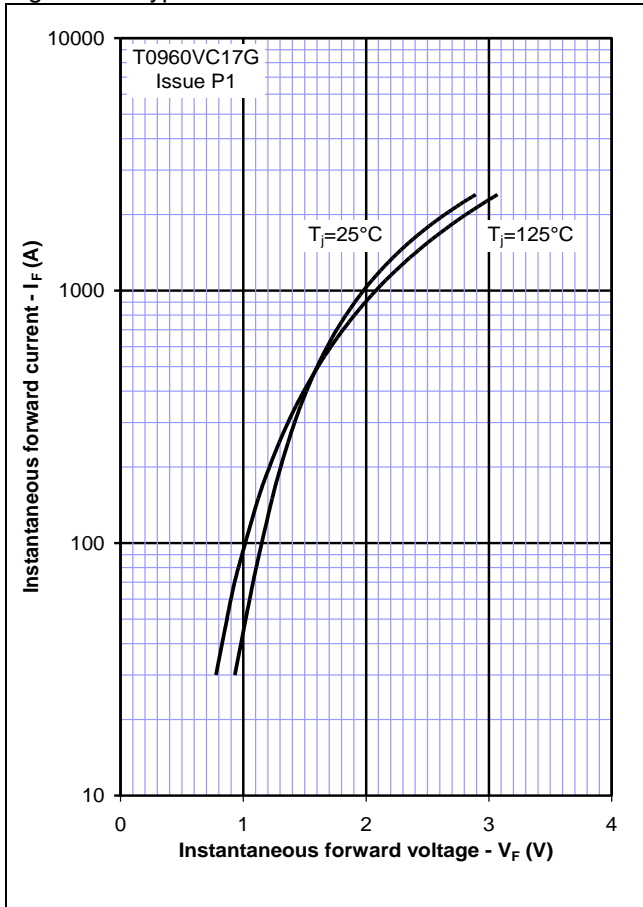


Figure 6 – Safe operating area (Diode)

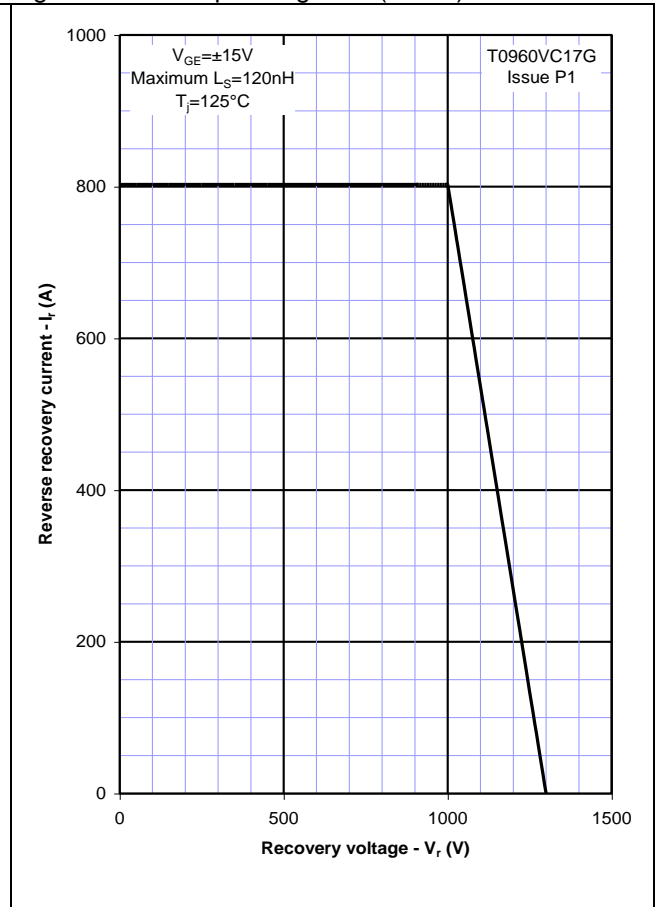


Figure 7 – Transient thermal impedance (IGBT)

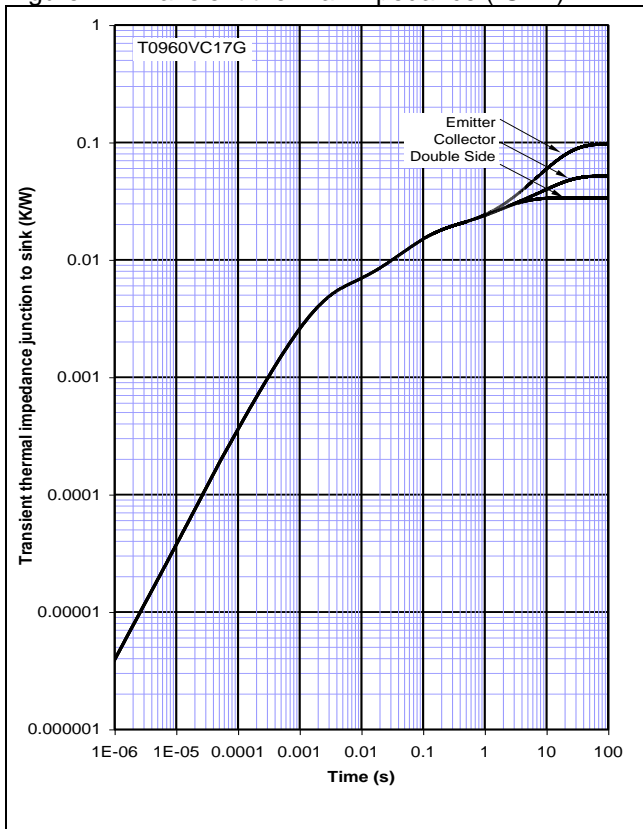
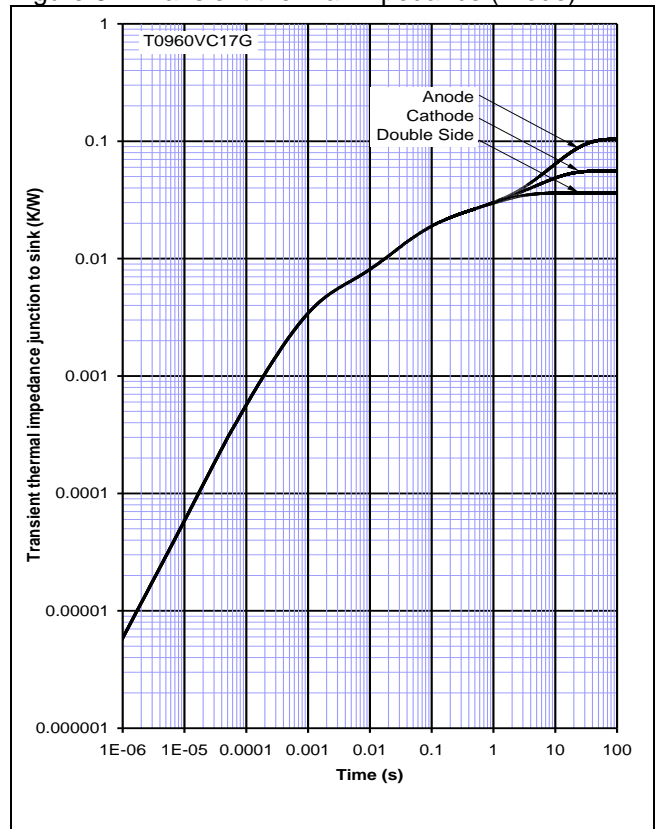
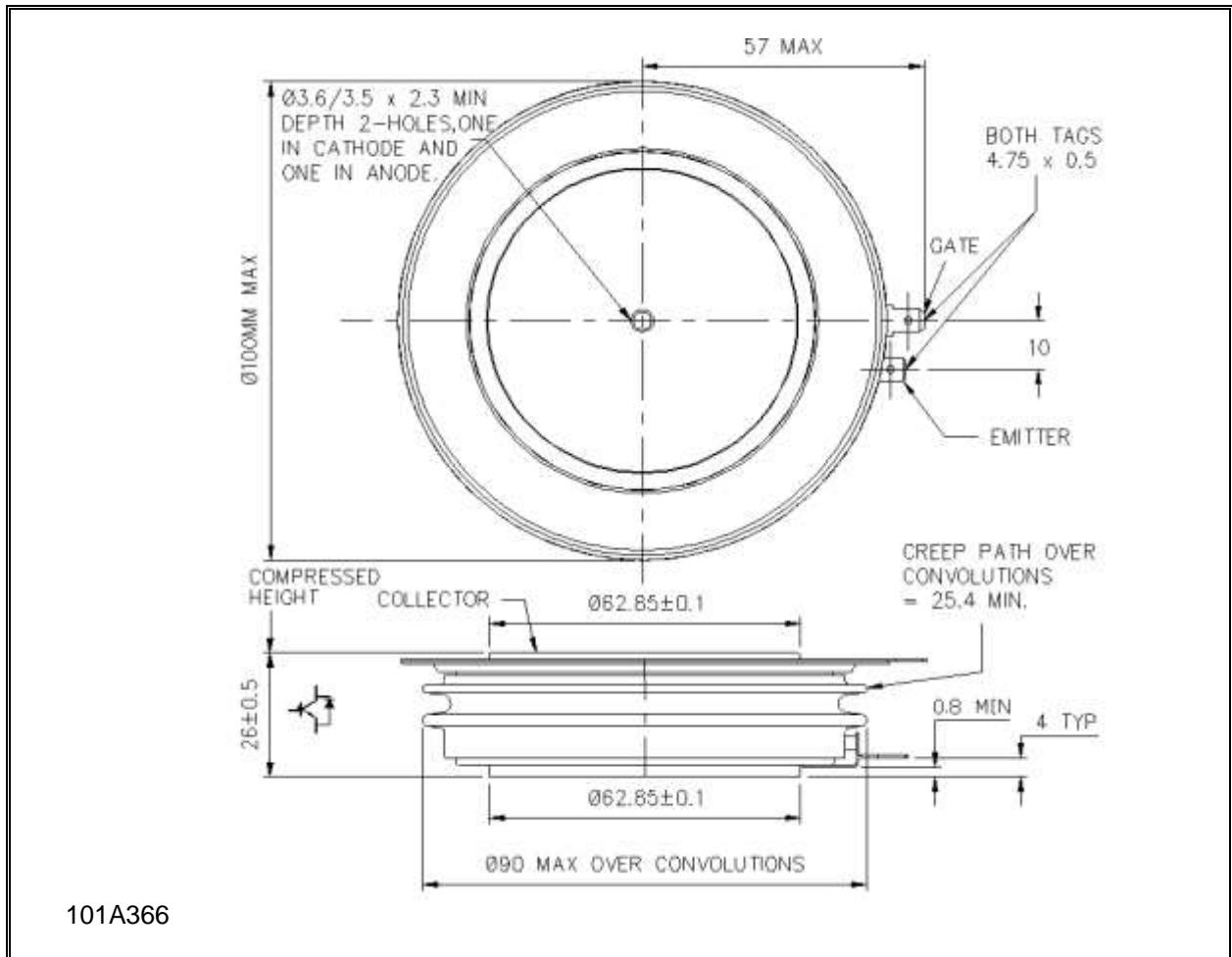


Figure 8 – Transient thermal impedance (Diode)



Outline Drawing & Ordering Information



ORDERING INFORMATION

(Please quote 10 digit code as below)

T0960	VC	17	G
Fixed type Code	Fixed Outline Code	Voltage Grade $V_{CES}/100$ 17	Fixed format code

Typical order code: T0960VC17G ($V_{CES} = 1700V$)

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